

Description

This -60V, -50A P-Channel MOSFET in a TO-252 Plastic Package.

Features

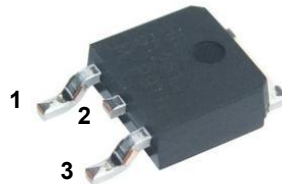
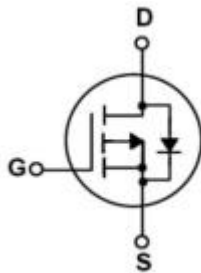
- Low $R_{DS(on)}$
- Low gate charge
- Low C_{rss}
- Fast switching
- HF Product.

Applications

Suited for low voltage applications such as automotive, DC/DC Converters, and high efficiency switching for power management in portable and battery operated products.

V_{DSS}	$R_{DS(on)}$ Typ	I_D
- 60V	30m Ω	- 50A

Equivalent Circuit & Pinning



PIN1 : Gate PIN 2 : Drain PIN 3 : Source

Absolute Maximum Ratings(Ta=25°C)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	-60	V
Drain Current		$I_D(T_c=25^\circ\text{C})$	-50	A
Drain Current - Pulsed		I_{DM}	-200	A
Gate-Source Voltage		V_{GS}	± 20	V
Power Dissipation		$P_D(T_c=25^\circ\text{C})$	85	W
Single Pulsed Avalanche Energy		E_{AS}	250	mJ
Avalanche Current(L=0.5mH)		I_{AS}	25	A
Junction and Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C
Thermal resistance, junction - ambient	$t \leq 10s$	$R_{\theta JA}$	25	°C / W
	Steady-State		50	
Thermal resistance, junction - case	Steady-State	$R_{\theta JC}$	1.5	

Electrical Characteristics(Ta=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V \quad I_D=-250\mu A$	-60	-68		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-60V \quad V_{GS}=0V$			-1.0	μA
		$V_{DS}=-48V \quad T_C=150^\circ\text{C}$			-10	
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 20V \quad V_{DS}=0V$			± 0.1	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS} \quad I_D=-250\mu A$	-1	-1.6	-3	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10V \quad I_D=-20A$		30	35	$m\Omega$
	$R_{DS(on)}$	$V_{GS}=-4.5V \quad I_D=-10A$		40	45	$m\Omega$
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V \quad I_S=-1A$			-1.2	V
Gate resistance	R_g			10		Ω
Input Capacitance	C_{iss}	$V_{DS}=-25V \quad V_{GS}=0V$ $f=1.0MHz$		3200		pF
Output Capacitance	C_{oss}			800		pF
Reverse Transfer Capacitance	C_{rss}			270		pF
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=-10V, V_{DS}=-30V,$ $I_D=-20A$		45		nC
Total Gate Charge	$Q_{g(4.5V)}$			23		
Gate Source Charge	Q_{gs}			9.3		
Gate Drain Charge	Q_{gd}			10.2		

Electrical Characteristics(Ta=25℃)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=-10V$ $V_{DS}=-30V$ $R_L=1.5$ $R_{GEN}=3\Omega$		12		ns
Turn-On Rise Time	t_r			14.5		
Turn-Off Delay Time	$t_{d(off)}$			38		
Turn-Off Fall Time	t_f			15		

Electrical Characteristic Curve

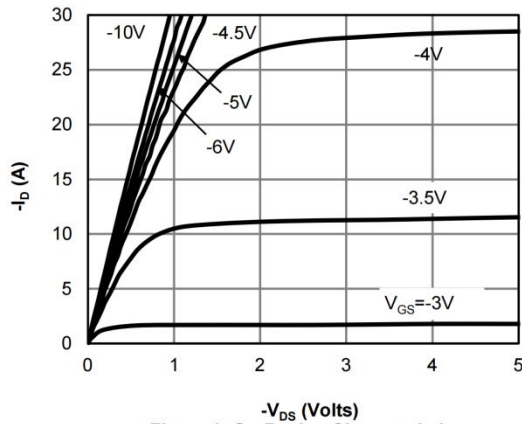


Figure 1: On-Region Characteristics

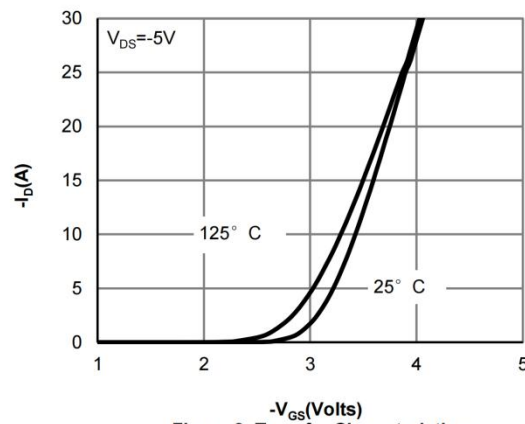


Figure 2: Transfer Characteristics

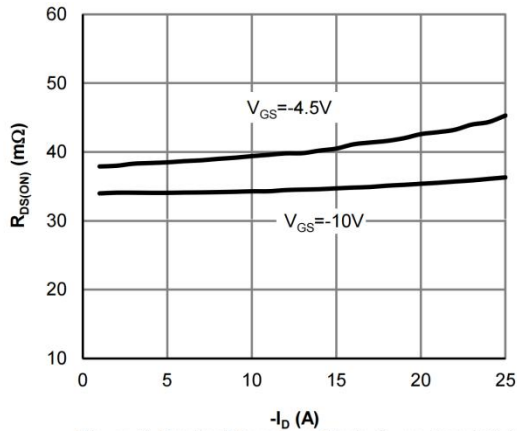


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

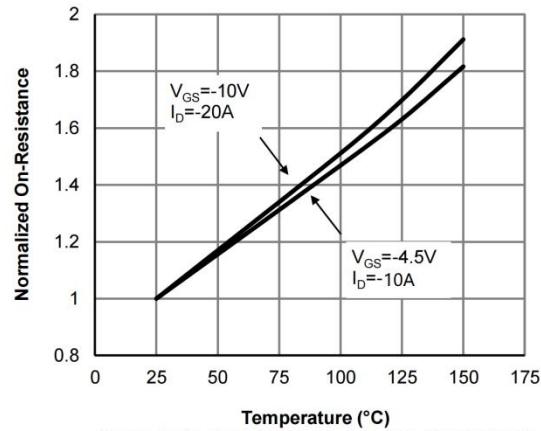


Figure 4: On-Resistance vs. Junction Temperature

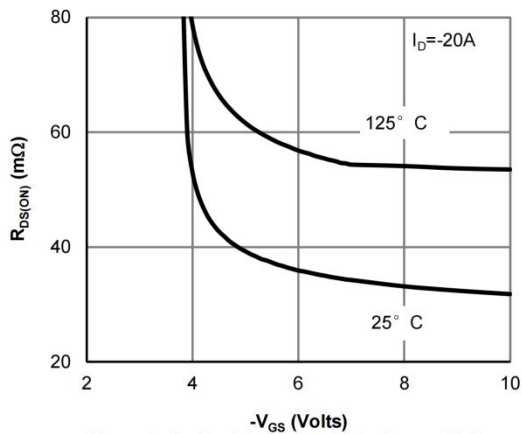


Figure 5: On-Resistance vs. Gate-Source Voltage

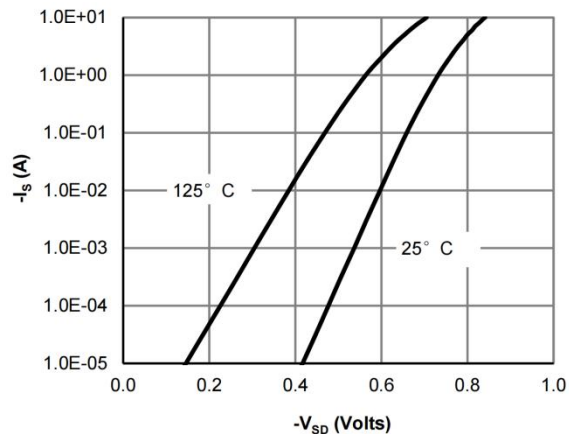
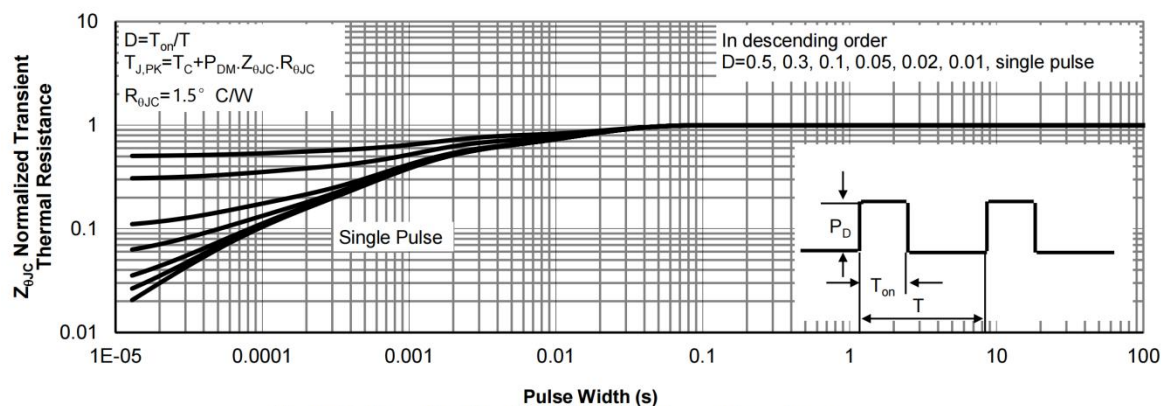
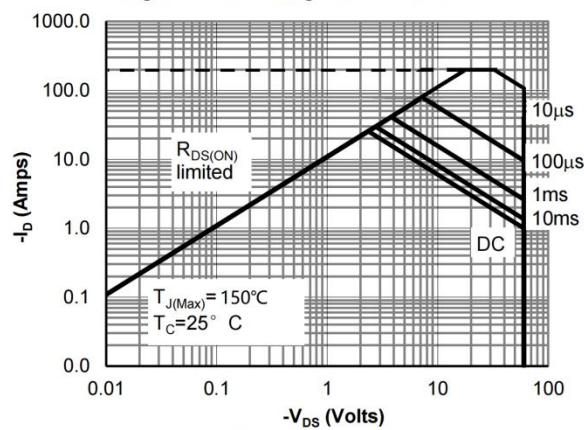
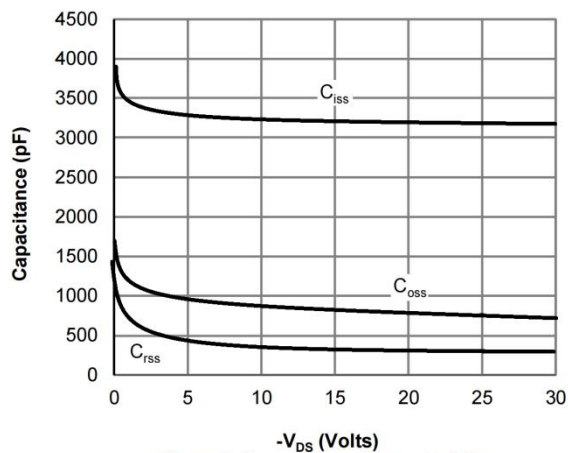
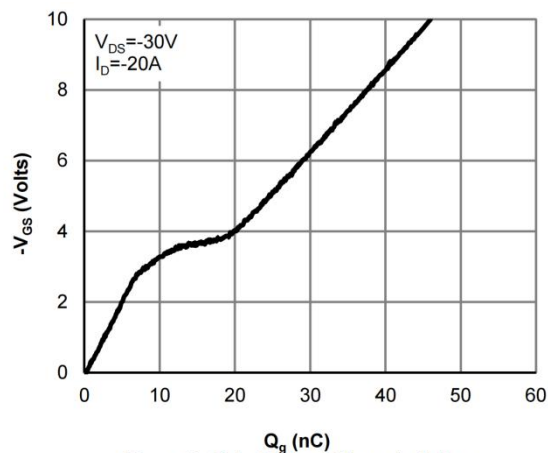
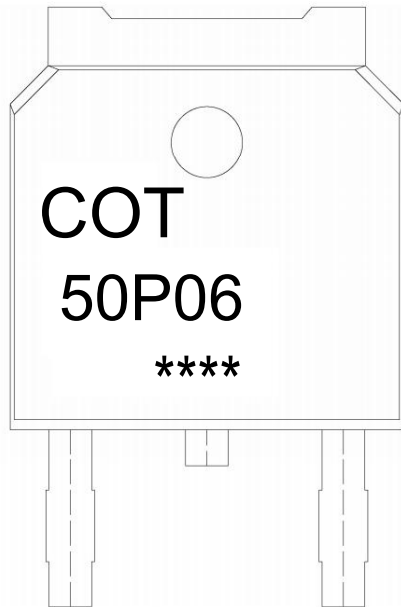


Figure 6: Body-Diode Characteristics

Electrical Characteristic Curve



Marking Instructions



Note:

COT: Company Logo

50P06: Product Type.

****: Lot No. Code, code change with Lot No.

Packaging SPEC.

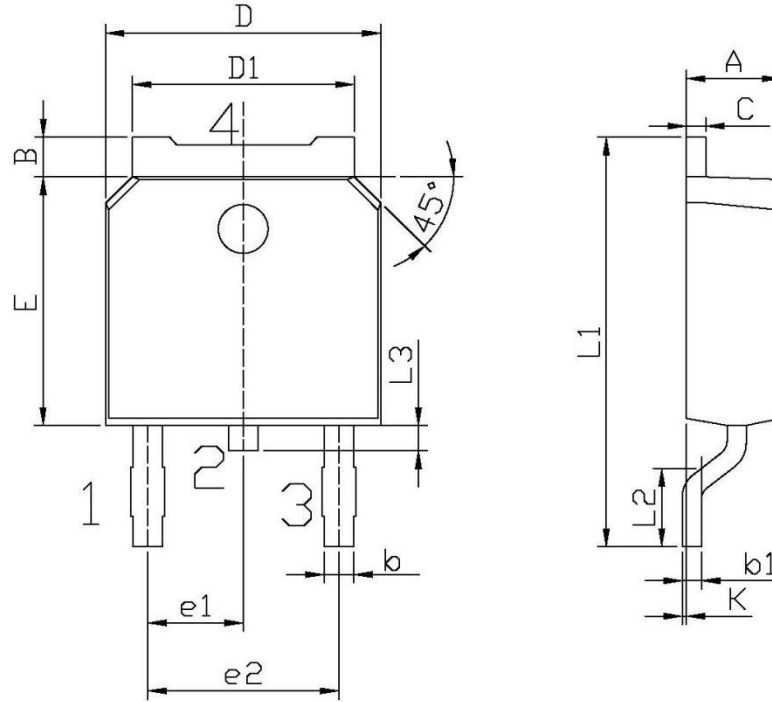
REEL INFORMATION

Package Type	Units					Dimension (unit: mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
TO-252	2,500	2	5,000	6	30,000	13" x16	360×360×50	380×335×366

TUBE INFORMATION

Package Type	Units					Dimension (unit: mm ³)		
	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Tube	Inner Box	Outer Box
TO-252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180

Package Outline Dimensions



单位: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	2.20	2.40	E	5.95	6.25
B	0.95	1.25	e1	2.24	2.34
b	0.70	0.90	e2	4.43	4.73
b1	0.45	0.55	L1	9.85	10.35
C	0.45	0.55	L2	1.70	2.00
D	6.45	6.75	L3	0.60	0.90
D1	5.10	5.50	K	0.00	0.10

TO-252